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Kind regards,

Team Nexperia



PMBT3906M

40 V, 200 mA PNP switching transistor

Rev. 01 — 22 July 2009

Product data sheet

1. Product profile

1.1 General description

PNP single switching transistor in a SOT883 (SC-101) leadless ultra small Surface-Mounted Device (SMD) plastic package.

NPN complement: PMBT3904M.

1.2 Features

- Single general-purpose switching transistor
- Board-space reduction
- AEC-Q101 qualified
- Ultra small SMD plastic package

1.3 Applications

■ General-purpose switching and amplification

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-200	mA
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V};$ $I_{C} = -10 \text{ mA}$	100	180	300	

2. Pinning information

Table 2. Pinning

Table 2.	ı ııııııg		
Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	1 3	3
3	collector	2 🔲	1—
		Transparent top view	1
		top view	2
			sym013



3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBT3906M	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883

4. Marking

Table 4. Marking codes

Type number	Marking code
PMBT3906M	6Q

5. Limiting values

Table 5. Limiting values

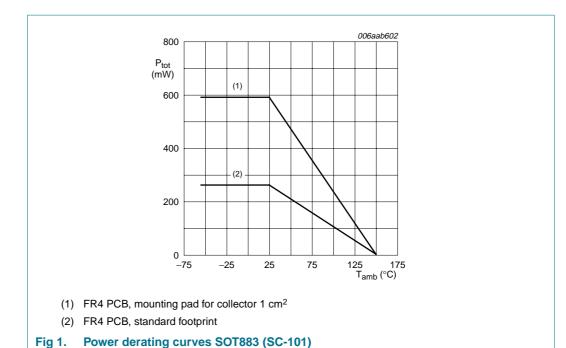
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I_{C}	collector current		-	-200	mA
I_{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1][2]	260	mW
			[1][3]	590	mW
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Reflow soldering is the only recommended soldering method.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

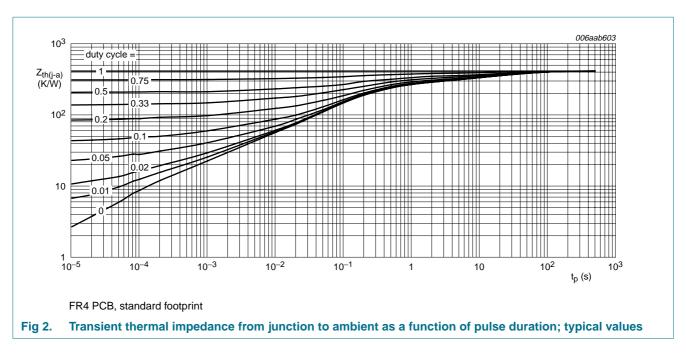


6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]	-	-	481	K/W
	junction to ambient		[1][3]	-	-	212	K/W

- [1] Reflow soldering is the only recommended soldering method.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².



7. Characteristics

Table 7. Characteristics

T_{amb} = 25 °C unless otherwise specified.

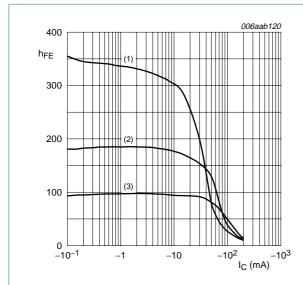
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-50	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -6 \text{ V}; I_C = 0 \text{ A}$	-	-	-50	nA
h _{FE}	DC current gain	$V_{CE} = -1 V$				
		$I_{C} = -0.1 \text{ mA}$	60	180	-	
		$I_C = -1 \text{ mA}$	80	180	-	
		$I_C = -10 \text{ mA}$	100	180	300	
		$I_C = -50 \text{ mA}$	60	130	-	
		$I_C = -100 \text{ mA}$	30	50	-	
V_{CEsat}	V _{CEsat} collector-emitter	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-100	-250	mV
	saturation voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-165	-400	mV
V_{BEsat}	base-emitter	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-750	-850	mV
	saturation voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-850	-950	mV
t _d	delay time	$V_{CC} = -3 \text{ V};$	-	-	35	ns
t _r	rise time	$I_C = -10 \text{ mA};$ $I_{Bon} = -1 \text{ mA};$	-	-	35	ns
t _{on}	turn-on time	$I_{Boff} = 1 \text{ mA}$	-	-	70	ns
ts	storage time	-	-	-	225	ns
t _f	fall time		-	-	75	ns
t _{off}	turn-off time		-	-	300	ns
C _c	collector capacitance	$V_{CB} = -5 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	4.5	pF

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Table 7. Characteristics ...continued

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _e	emitter capacitance	$V_{EB} = -500 \text{ mV};$ $I_C = i_c = 0 \text{ A}; f = 1 \text{ MHz}$	-	-	10	pF
f _T	transition frequency	$V_{CE} = -20 \text{ V};$ $I_{C} = -10 \text{ mA};$ $f = 100 \text{ MHz}$	250	-	-	MHz
NF	noise figure	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}; R_{S} = 1 k\Omega;$ f = 10 Hz to 15.7 kHz	-	-	4	dB



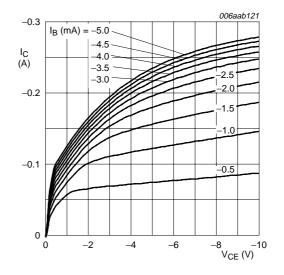


⁽¹⁾ $T_{amb} = 150 \, ^{\circ}C$

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(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 3. DC current gain as a function of collector current; typical values

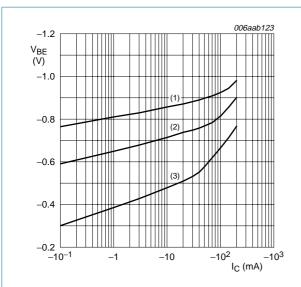


 $T_{amb} = 25 \, ^{\circ}C$

Fig 4. Collector current as a function of collector-emitter voltage; typical values

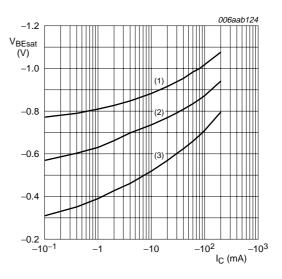
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⁽²⁾ $T_{amb} = 25 \, ^{\circ}C$



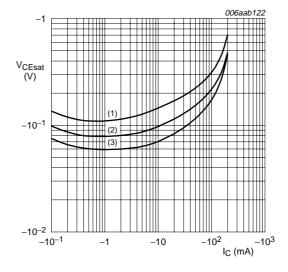
- $V_{CE} = -1 V$
- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 5. Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 10$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

Fig 6. Base-emitter saturation voltage as a function of collector current; typical values

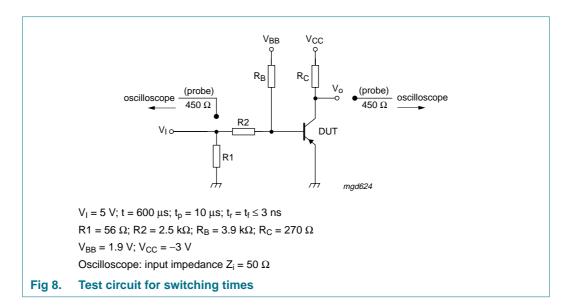


- $I_{\rm C}/I_{\rm B}=10$
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

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Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

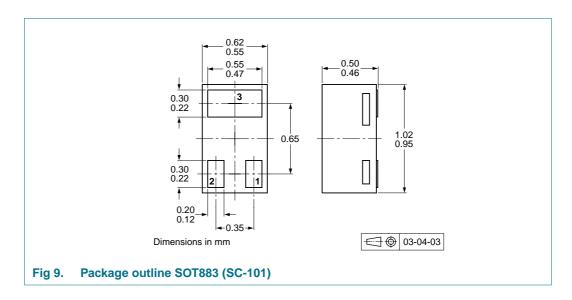
8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



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40 V, 200 mA PNP switching transistor

10. Packing information

Table 8. **Packing methods**

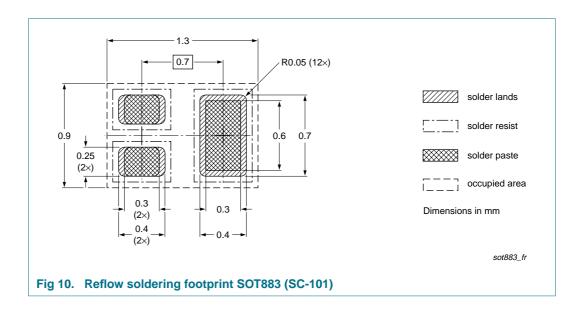
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
PMBT3906M	SOT883	2 mm pitch, 8 mm tape and reel	-315

^[1] For further information and the availability of packing methods, see Section 14.

11. Soldering

Product data sheet





12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMBT3906M_1	20090722	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMBT3906M

40 V, 200 mA PNP switching transistor

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